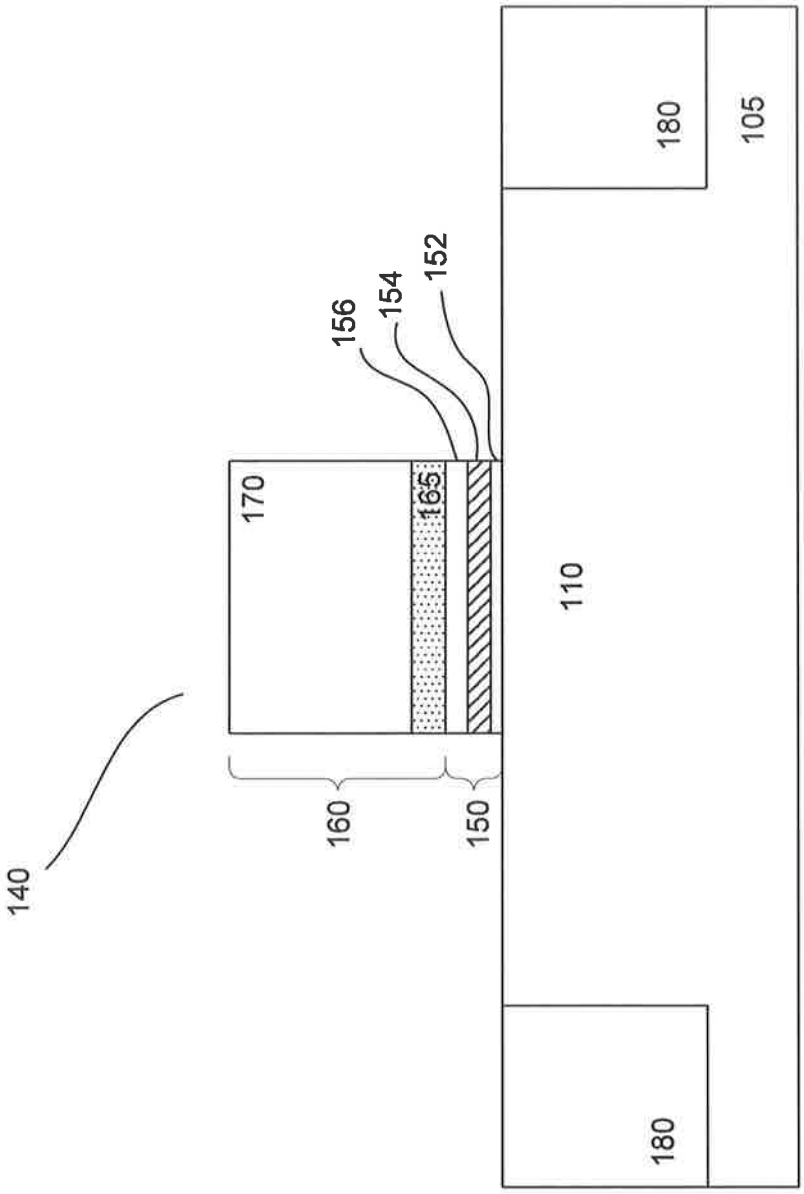


Fig. 1a

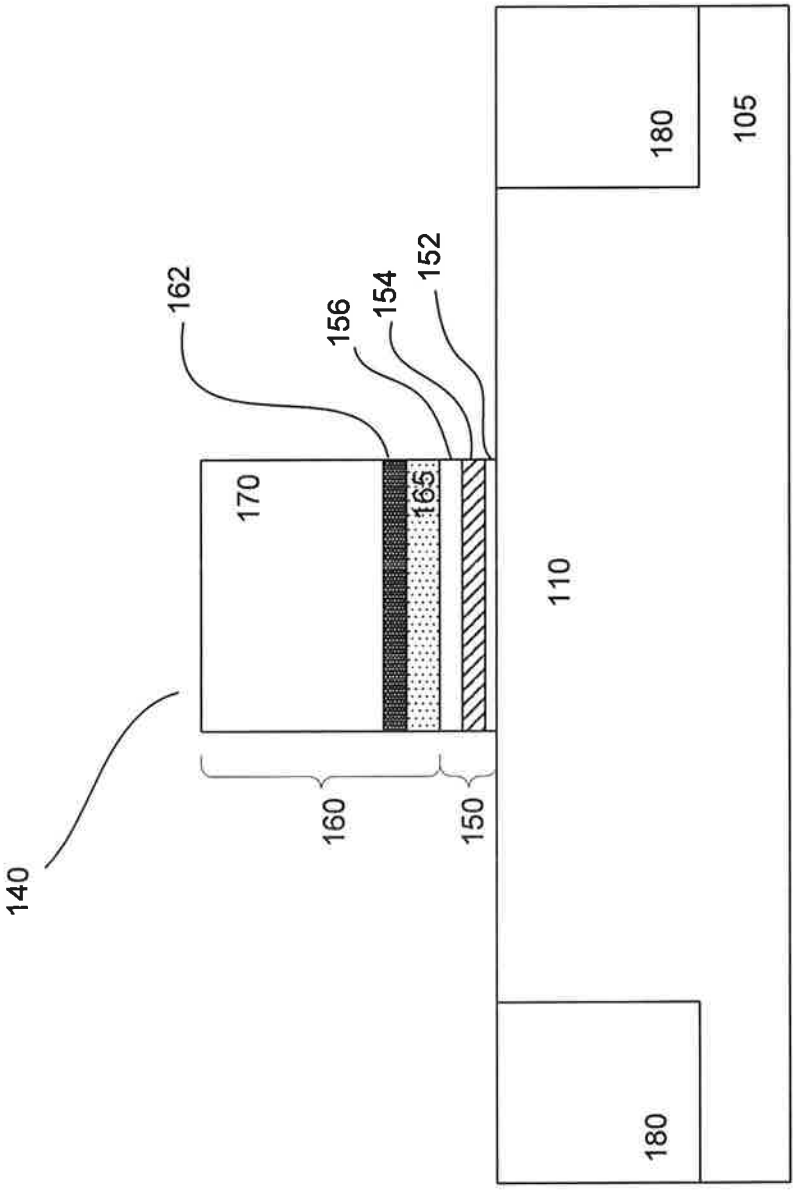
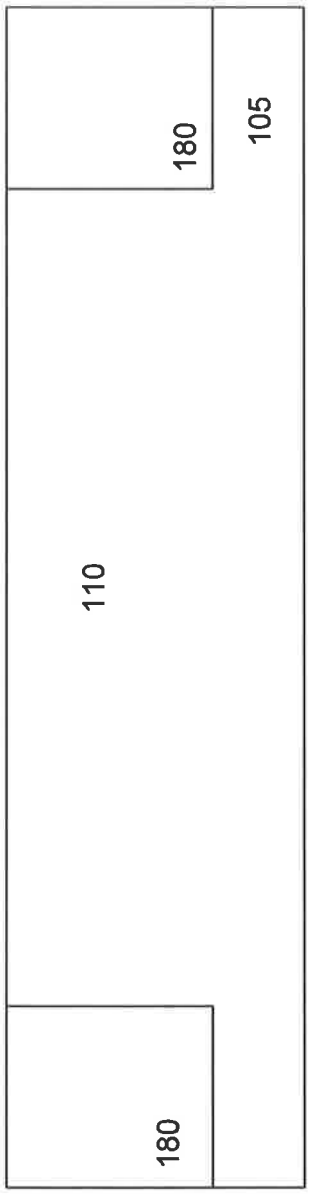


Fig. 1b



200

Fig. 2a

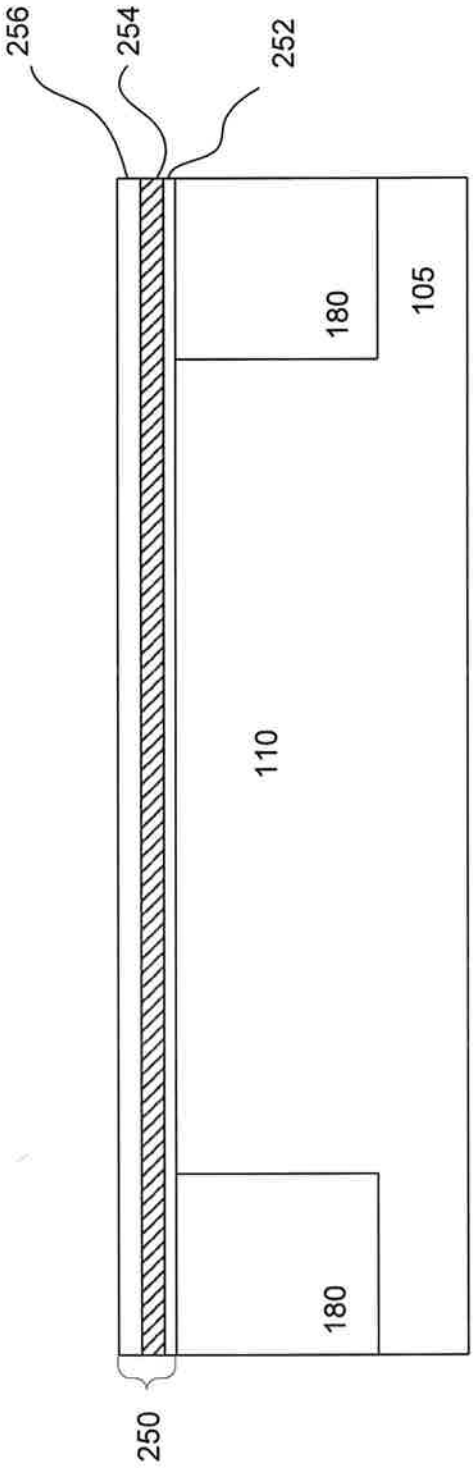


Fig. 2b

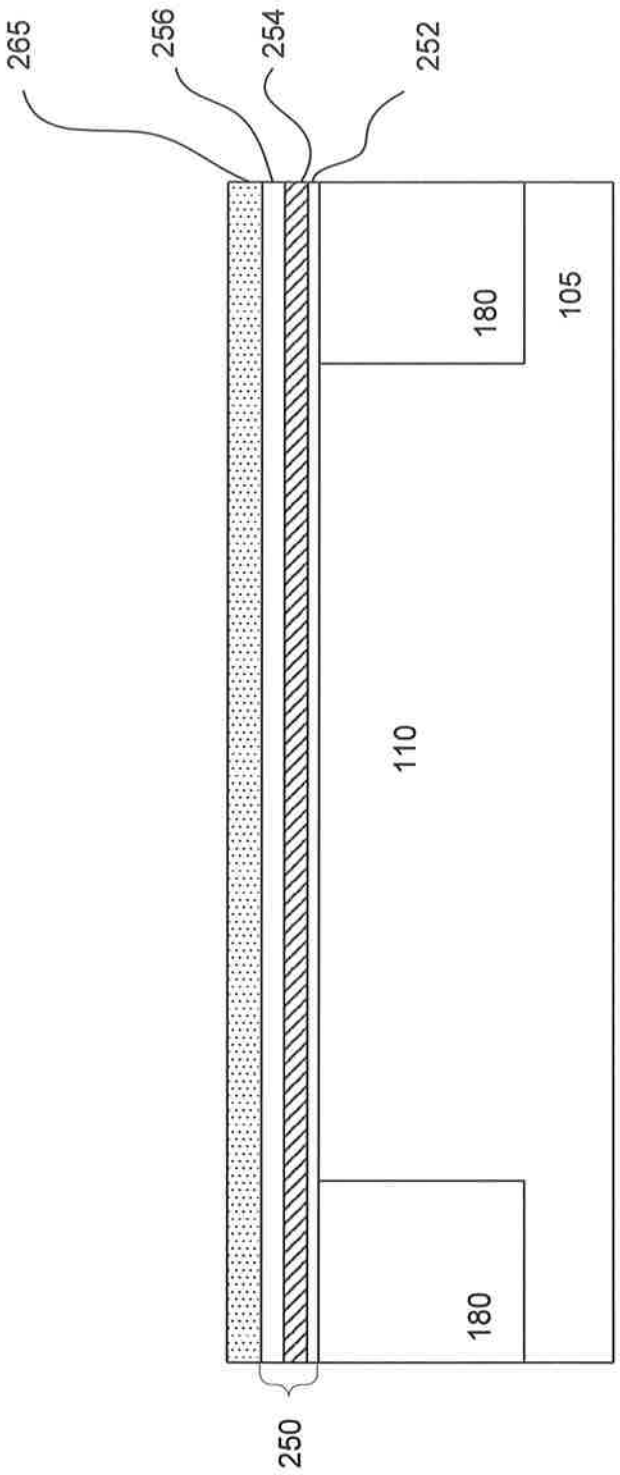
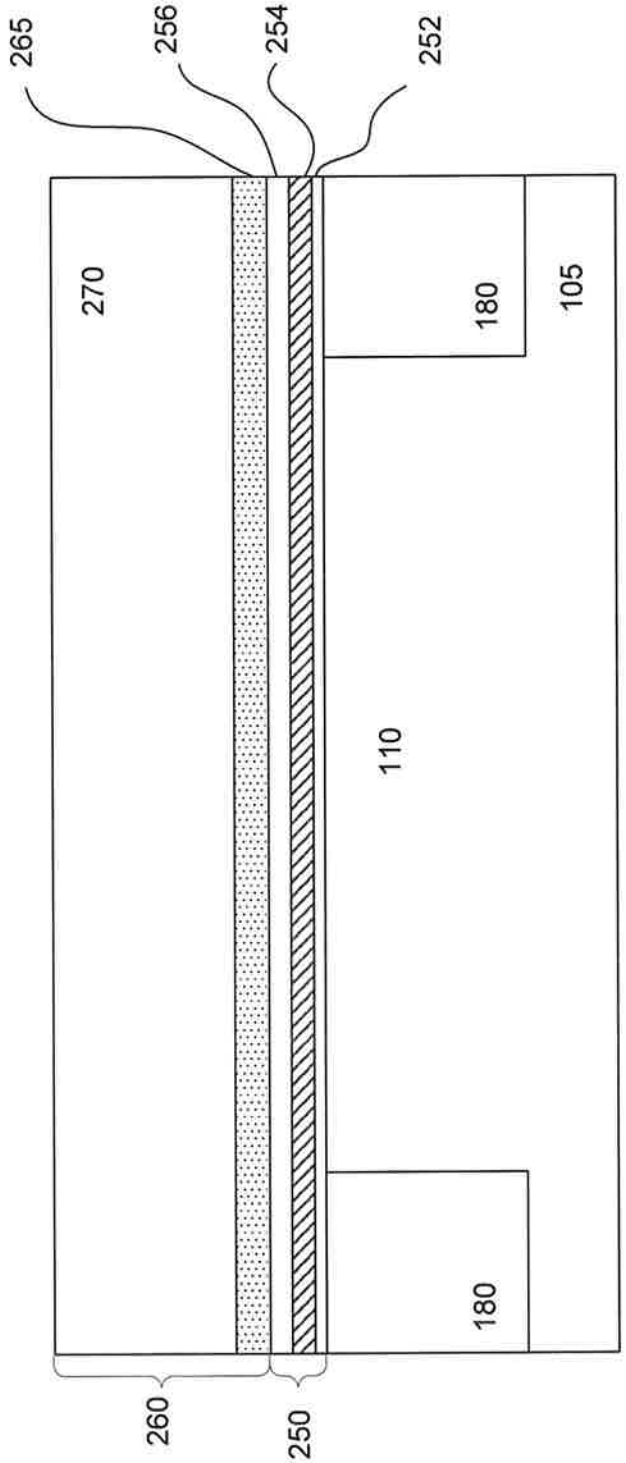


Fig. 2c



200

Fig. 2d

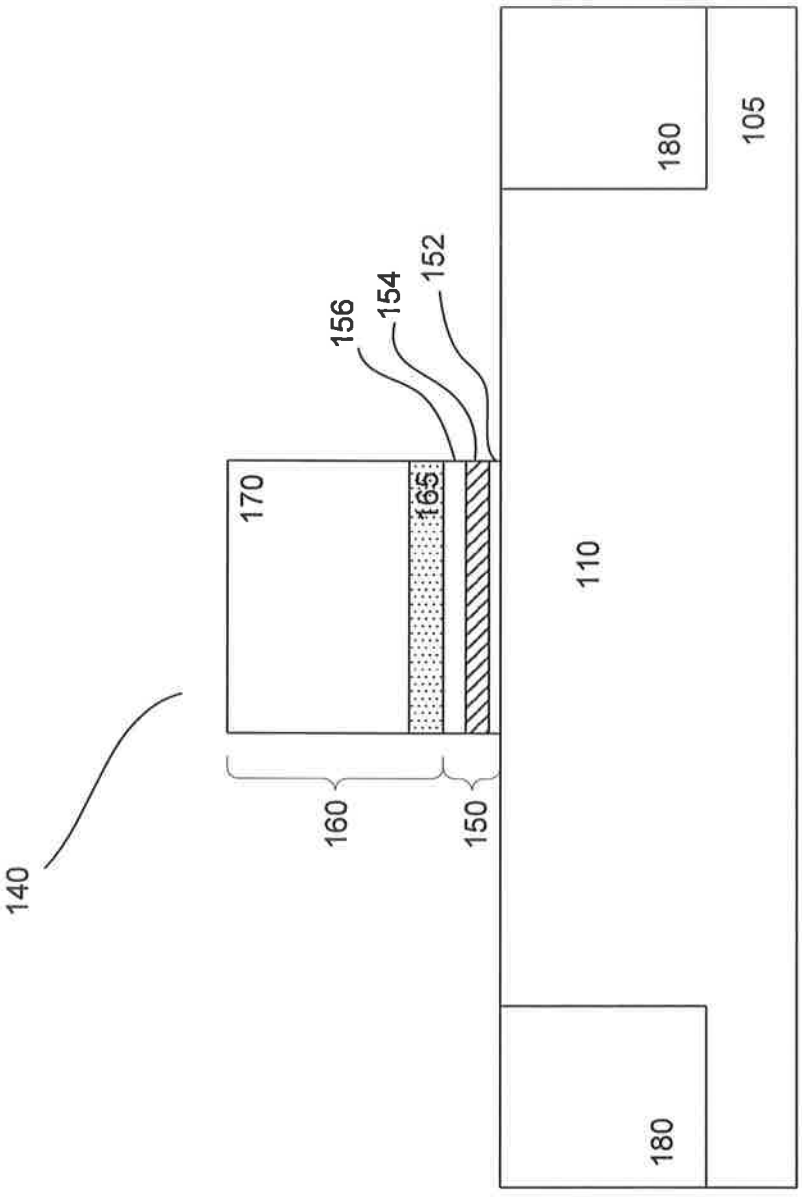
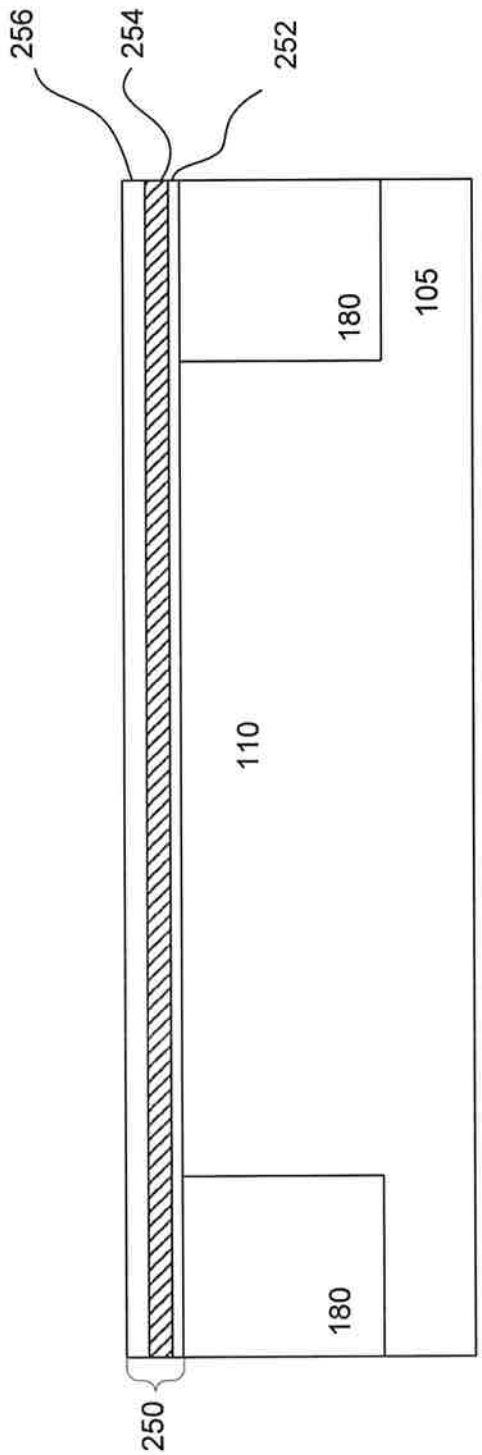


Fig. 2e



300

Fig. 3a

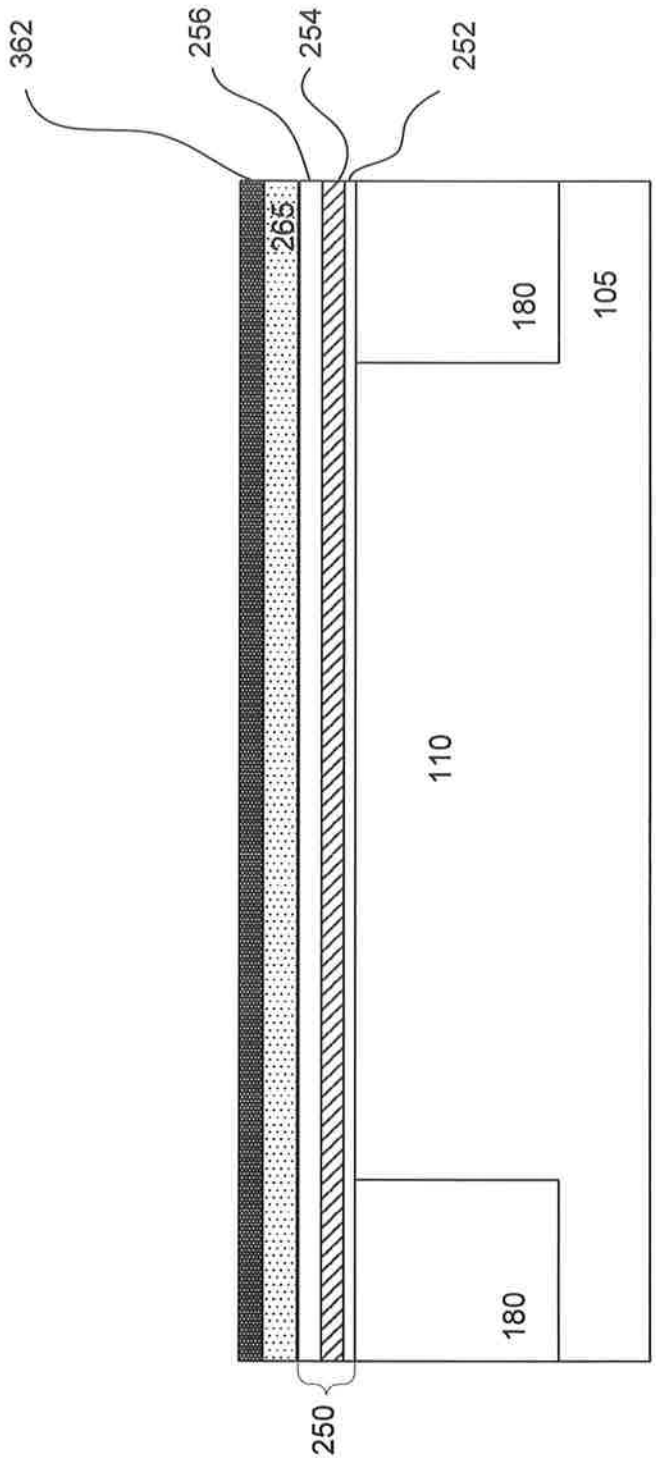


Fig. 3b

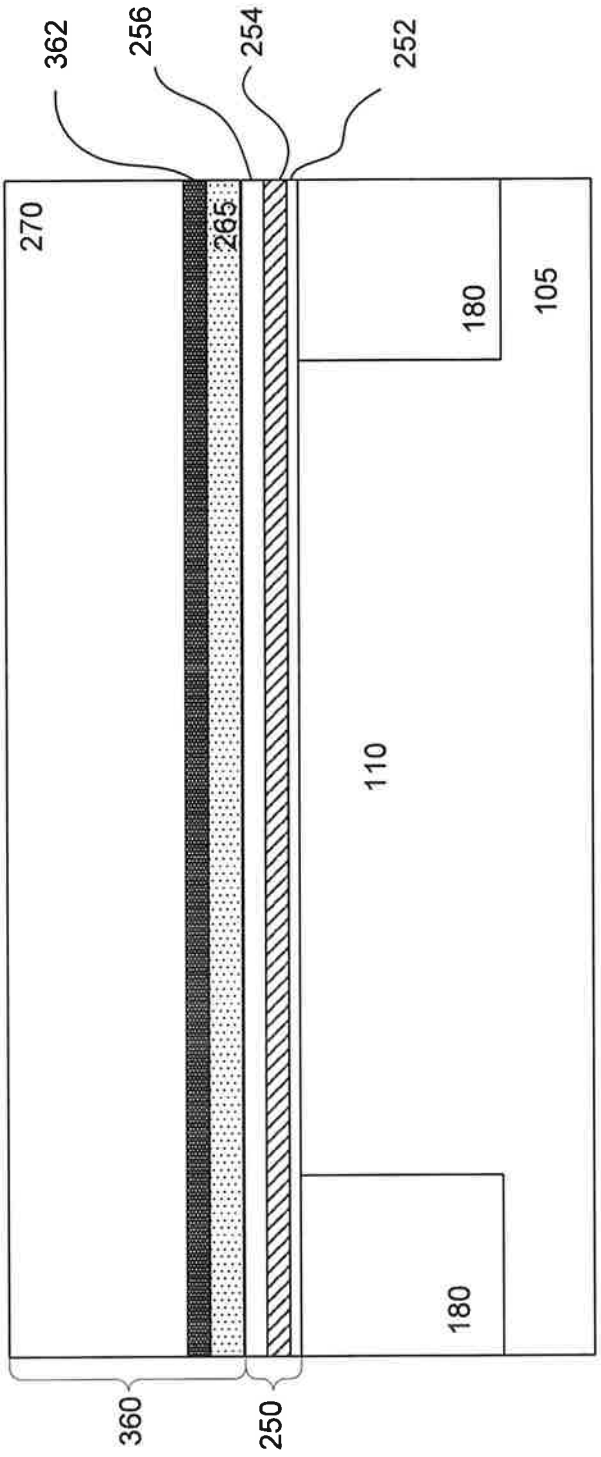


Fig. 3c

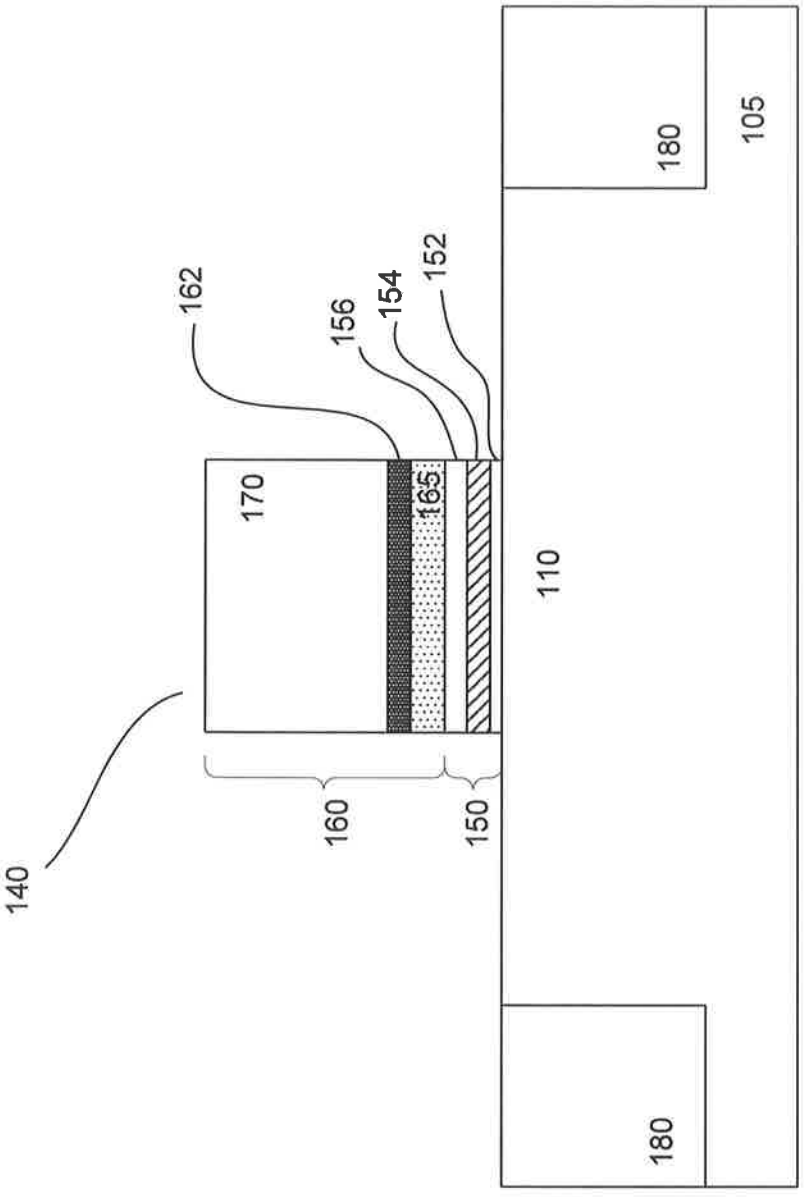


Fig. 3d

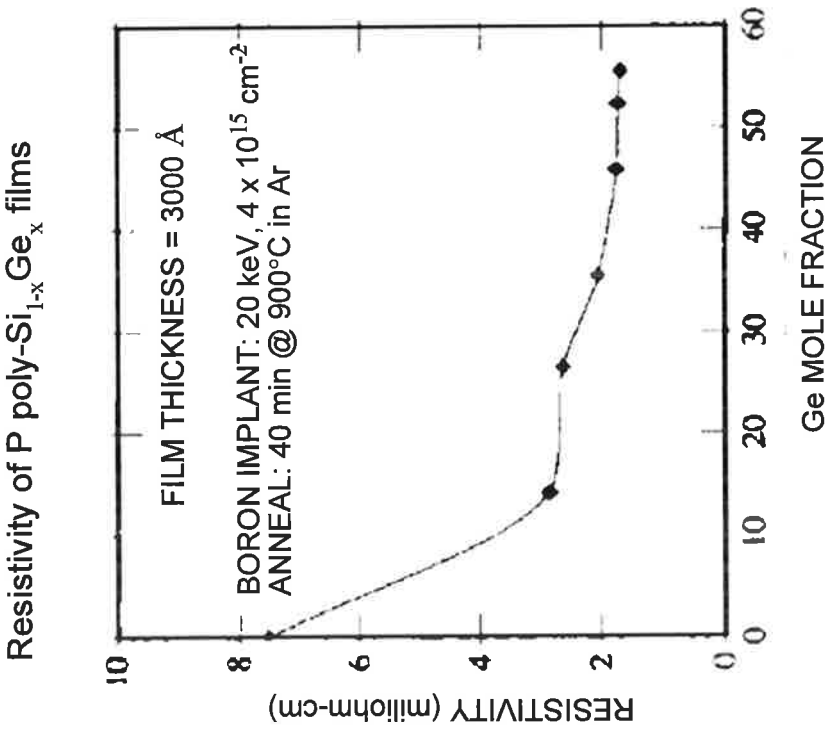

Resistivity of P poly-Si1-xGex films
FILM THICKNESS = 3000 Å
BORON IMPLANT: 20 keV, 4 x 10^15 cm^-2
ANNEAL: 40 min @ 900°C in Ar
RESISTIVITY (milliohm-cm)
Ge MOLE FRACTION
0
2
4
6
8
10
0
10
20
30
40
50
60

Fig. 4

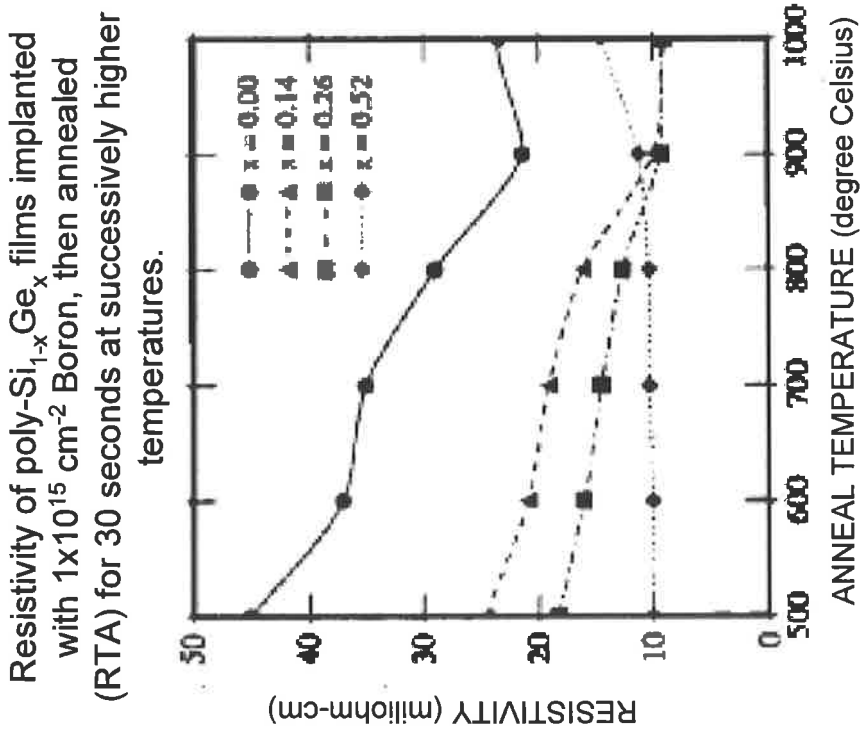

Resistivity of poly-Si1-xGex films implanted with 1x10^15 cm^-2 Boron, then annealed (RTA) for 30 seconds at successively higher temperatures.
RESISTIVITY (milliohm-cm)
ANNEAL TEMPERATURE (degree Celsius)
x = 0.00
x = 0.14
x = 0.26
x = 0.52
50
40
30
20
10
0
500
600
700
800
900
1000

Fig. 5